

350V N-Channel MOSFET

General Features

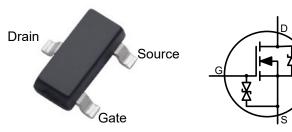
- ➤ ESD improved Capability
- Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure
- > Fast Switching Speed
- ➤ RoHS Compliant
- ➤ Halogen-free available

Applications

- ➤ High Efficiency SMPS
- ➤ Adaptor/Charger
- > Active PFC

| BVDSX | RDS(ON) (Max.) | ID | | |
|-------|----------------|-------|--|--|
| 350V | 15 Ω | 200mA | | |

SOT-23



Ordering Information

| Part Number | Part Number Package | | Remark |
|-------------|---------------------|-----|--------------|
| FTZ15N35G | SOT-23 | N35 | Halogen Free |

Absolute Maximum Ratings

 $T_A=25$ °C unless otherwise specified

| Symbol | Parameter | FTZ15N35G | Unit | |
|-------------------------------------|--|------------|--------------|--|
| $V_{ m DSX}$ | Drain-to-Source Voltage ^[1] | 350 | V | |
| V _{DGX} | Drain-to-Gate Voltage ^[1] | 350 | V | |
| I_D | Continuous Drain Current | 0.2 | | |
| I_{DM} | Pulsed Drain Current ^[2] | 0.6 | A | |
| P_D | Power Dissipation | 0.50 | W | |
| V_{GS} | Gate-to-Source Voltage | ±20 | V | |
| V _{ESD(G-S)} | Gate Source ESD IEC, C=150pF, R=330 Ω | 200 | V | |
| $T_{\rm L}$ | Soldering Temperature Distance of 1.6mm from case for 10 seconds | 300 | \mathbb{C} | |
| T _J and T _{STG} | Operating and Storage Temperature Range | -55 to 150 | | |

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

| Symbol | Parameter | FTZ15N35G | Unit |
|----------------|---|-----------|------|
| $R_{	heta JA}$ | Thermal Resistance, Junction-to-Ambient | 250 | K/W |

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Electrical Characteristics

OFF Characteristics

T_A =25 °C unless otherwise specified

| Symbol | Parameter | Min. | Typ. | Max. | Unit | Test Conditions |
|--------------------------------------|--|------|------|------|------|---|
| $\mathrm{BV}_{\mathrm{DSX}}$ | Drain-to-Source Breakdown Voltage | 350 | | | V | $V_{GS}=0V,I_D=250\mu A$ |
| $\triangle BV_{DSS}/\triangle T_{J}$ | Breakdown Voltage Temperature Coefficient | | 0.35 | | V/℃ | Reference to 25° C, $I_D=250\mu A$ |
| | | | | 1 | μΑ | $V_{DS}=350V$, $V_{GS}=0V$ |
| I_{DSS} | Drain-to-Source Leakage Current | | | 100 | uA | V_{DS} =350V, V_{GS} = 0V T_J =125°C |
| т | Gate-to-Source Leakage Current | | | 20 | uA | V _{GS} =+20V, V _{DS} =0V |
| I_{GSS} | | | | -20 | | V_{GS} =-20V, V_{DS} =0V |

ON Characteristics

$T_A = 25^{\circ}C$ unless otherwise specified

| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
|---------------------|--------------------------------------|------|------|------|------|----------------------------------|
| R _{DS(ON)} | Static Drain-to-Source On-Resistance | | 8 | 15 | Ω | $V_{GS}=10V$, $I_D=200mA^{[3]}$ |
| V _{GS(TH)} | Gate Threshold Voltage | 1 | | 3 | V | $V_{GD} = 0V, I_D = 250 \mu A$ |

Dynamic Characteristics

Essentially independent of operating temperature

| | | | | | F | one of operating temperature |
|---------------------|------------------------------|------|-------|------|------|---|
| Symbol | Parameter | Min. | Тур. | Max. | Unit | Test Conditions |
| C_{ISS} | Input Capacitance | | 32.58 | | | V _{GS} =0V |
| Coss | Oput Capacitance | | 5.36 | | pF | $V_{DS}=25V$ f=1.0MHz |
| C_{RSS} | Reverse Transfer Capacitance | | 0.75 | | | |
| $t_{d(ON)}$ | Turn-on Delay Time | | 14 | | | |
| t_{rise} | Rise Time | | 10 | | 40.0 | $V_{DD} = 25V, I_D = 80mA$ $R_G = 25Ohm$ $V_{GS} = 10V \sim 0V$ |
| $t_{d(OFF)}$ | Turn-off Delay Time | | 24 | | ns | |
| t_{fall} | Fall Time | | 36 | | | |

Source-Drain Diode Characteristics

T_A=25°C unless otherwise specified

| Symbol | Parameter | Min | Тур. | Max. | Units | Test Conditions |
|-------------------|-----------------------|-----|------|------|-------|----------------------------------|
| V_{SD} | Diode Forward Voltage | | | 1.8 | V | I_{SD} =200 mA, V_{GS} = 0 V |

NOTE:

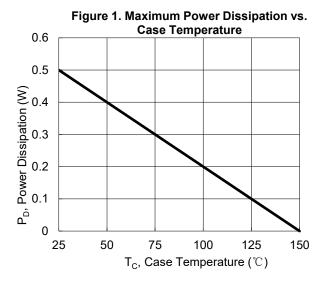
- [1] $T_J = +25^{\circ}C$ to $+150^{\circ}C$
- [2] Repetitive rating, pulse width limited by maximum junction temperature.
- [3] Pulse width \(380\mu s; \) duty cycle \(\le 2\% \).

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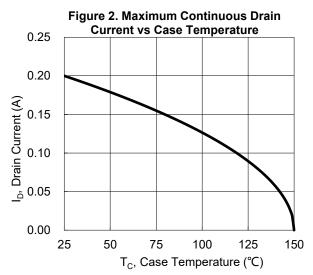
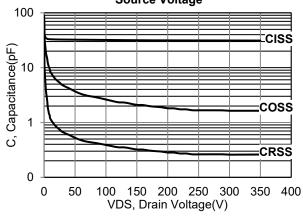


Figure 3. Typical Capacitance vs. Drain-to-Source Voltage



Switching Waveforms and Test Circuit

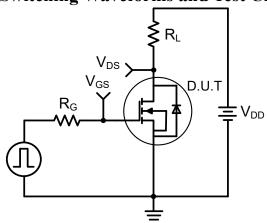


Figure 4. Resistive Switching Test Circuit

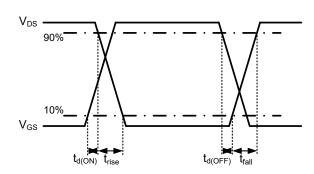
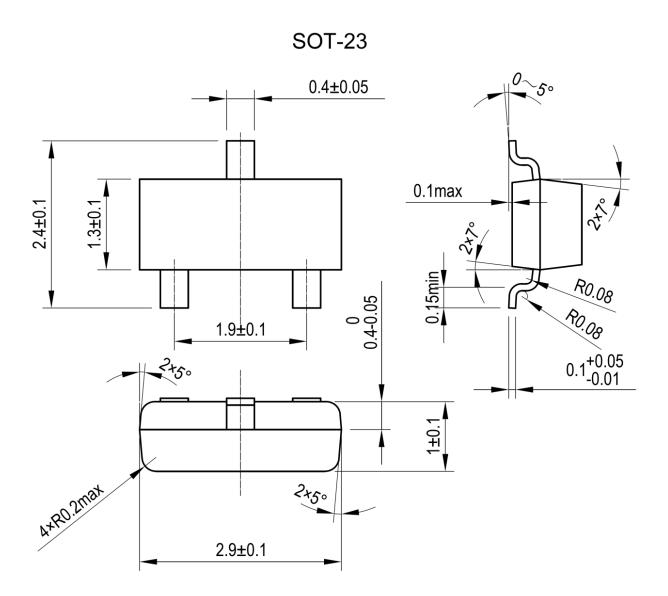


Figure 5. Resistive Switching Waveforms



Package Dimensions





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